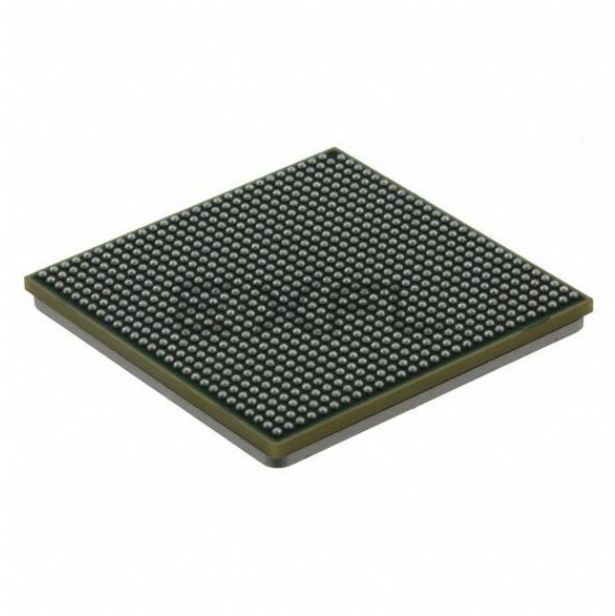

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8541pxaqf

  - Selectable hardware-enforced coherency
  - Selectable clock source (SYSCLK or independent PCI_CLK)
- Power management
  - Fully static 1.2-V CMOS design with 3.3- and 2.5-V I/O
  - Supports power save modes: doze, nap, and sleep
  - Employs dynamic power management
  - Selectable clock source (sysclk or independent PCI_CLK)
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- IEEE Std 1149.1™-compatible, JTAG boundary scan
- 783 FC-PBGA package

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8541E. The MPC8541E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

3 Power Characteristics

The estimated typical power dissipation for this family of PowerQUICC III devices is shown in Table 4.

Table 4. Power Dissipation(1) (2)

CCB Frequency (MHz)	Core Frequency (MHz)	V_{DD}	Typical Power(3)(4) (W)	Maximum Power(5) (W)
200	400	1.2	4.4	6.1
	500	1.2	4.7	6.5
	600	1.2	5.0	6.8
267	533	1.2	4.9	6.7
	667	1.2	5.4	7.2
	800	1.2	5.8	8.6
333	667	1.2	5.5	7.4
	833	1.2	6.0	8.8
	1000(6)	1.3	9.0	12.2

Notes:

1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}.
2. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance. Any customer design must take these considerations into account to ensure the maximum 105 degrees junction temperature is not exceeded on this device.
3. Typical power is based on a nominal voltage of V_{DD} = 1.2V, a nominal process, a junction temperature of T_j = 105° C, and a Dhrystone 2.1 benchmark application.
4. Thermal solutions likely need to design to a value higher than Typical Power based on the end application, T_A target, and I/O power
5. Maximum power is based on a nominal voltage of V_{DD} = 1.2V, worst case process, a junction temperature of T_j = 105° C, and an artificial smoke test.
6. The nominal recommended V_{DD} = 1.3V for this speed grade.

Notes:

1.

2.

3.

4.

5.

6.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
$\overline{MCS}$(n) output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCX}	 2.0 2.65 3.8	—	ns	4
MCK to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHMH}	 –0.9 –1.1 –1.2	 0.3 0.5 0.6	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 900 900 1200	—	ps	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 900 900 1200	—	ps	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.9$	$-0.5 \times t_{MCK} + 0.3$	ns	7
MDQS epilogue end	t_{DDKLME}	–0.9	0.3	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{MCK}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{MCK}$ can be shifted in 1/4 applied cycle increments through the Clock Control Register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{MCK}$, $\overline{MCS}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle. The MCSx pins are separated from the ADDR/CMD (address and command) bus in the HW spec. This was separated because the MCSx pins typically have different loadings than the rest of the address and command bus, even though they have the same timings.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). In the source synchronous mode, MDQS can launch later than MCK by 0.3 ns at the maximum. However, MCK may launch later than MDQS by as much as 0.9 ns. t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this typically is set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8555E PowerQUICC™ III Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8541E.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the MPC8541E. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 provides the AC test load for the DDR bus.

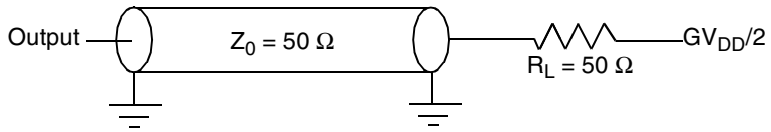


Figure 6. DDR AC Test Load

Table 15. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V_{TH}	MV_{REF} ± 0.31 V	V	1
V_{OUT}	0.5 × GV_{DD}	V	2

Notes:
1. Data input threshold measurement point.
2. Data output measurement point.

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8541E.

7.1 DUART DC Electrical Characteristics

Table 16 provides the DC electrical characteristics for the DUART interface of the MPC8541E.

Table 16. DUART DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [1] = 0 V or $V_{IN} = V_{DD}$	—	±5	μA
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –100 μA	OV_{DD} – 0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 100 μA	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

Figure 14 shows the RBMII and RTBI AC timing and multiplexing diagrams.

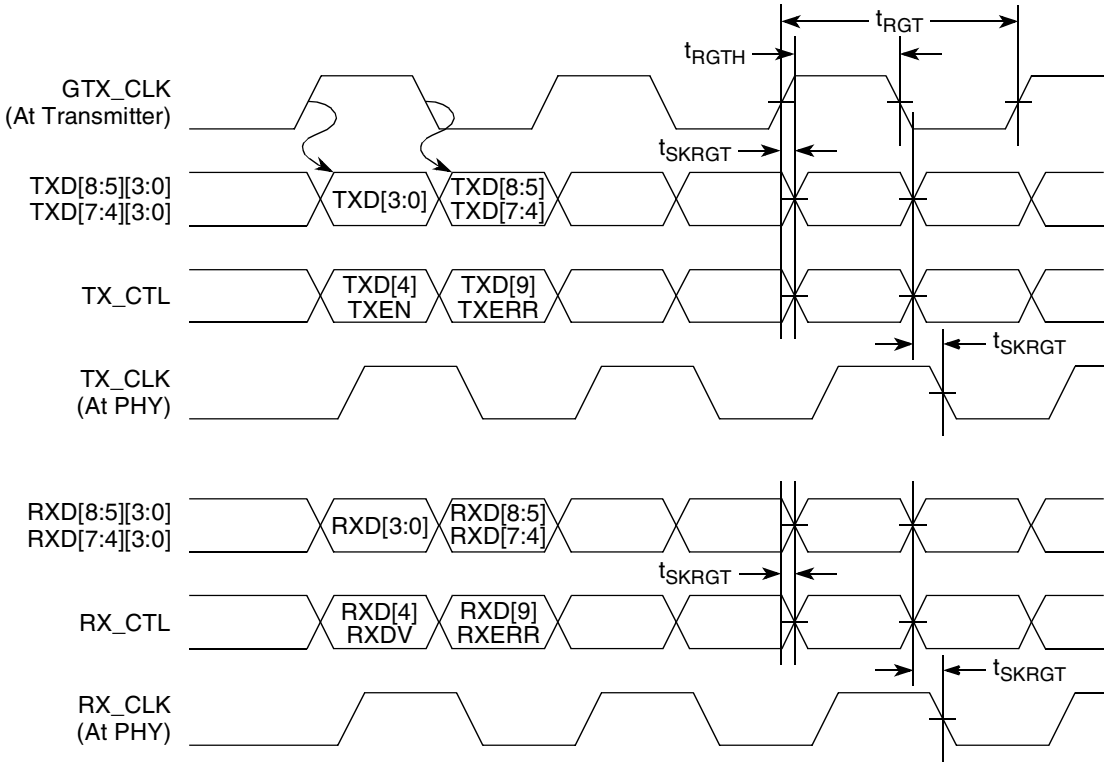


Figure 14. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC) (10/100/1000 Mbps)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 27.

Table 27. MII Management DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		3.13	3.47	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.10	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		1.70	—	V
Input low voltage	V_{IL}	—		—	0.90	V

Figure 15 shows the MII management AC timing diagram.

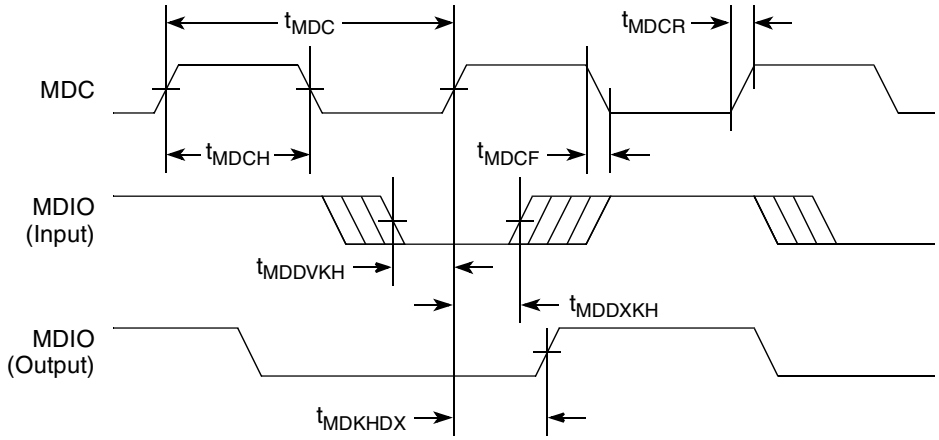


Figure 15. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8541E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [1] = 0 V or $V_{IN} = V_{DD}$	—	±5	μA
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –2mA	OV_{DD} –0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 2mA	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

Table 30. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKHOZ2}$	—	2.8	ns	5, 9
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			4.2		

Notes:
1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for DLL enabled to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Table 31 describes the general timing parameters of the local bus interface of the MPC8541E with the DLL bypassed.

Table 31. Local Bus General Timing Parameters—DLL Bypassed

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay	—	t_{LBKHKT}	1.8	3.4	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$	—	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	5.2	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	5.1	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	–1.3	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	–0.8	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	—	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV1}$	—	0.5	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.0		
Local bus clock to data valid for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV2}$	—	0.7	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.2		

Table 31. Local Bus General Timing Parameters—DLL Bypassed (continued)

Parameter	Configuration [7]	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to address valid for LAD	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOV3}$	—	0.8	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.3		
Output hold from local bus clock (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOX1}$	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)		–1.8			
Output hold from local bus clock for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOX2}$	–2.7	—	ns	3
	$\overline{\text{LWE}}[0:1]$ = 11 (default)		–1.8			
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOZ1}$	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.4		
Local bus clock to output high impedance for LAD/LDP	$\overline{\text{LWE}}[0:1]$ = 00	$t_{LBKLOZ2}$	—	1.0	ns	5
	$\overline{\text{LWE}}[0:1]$ = 11 (default)			2.4		

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for DLL enabled mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of local bus clock for DLL bypass mode to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins $\overline{\text{LWE}}[0:1]$.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
8. Guaranteed by characterization.
9. Guaranteed by design.

Figure 16 provides the AC test load for the local bus.

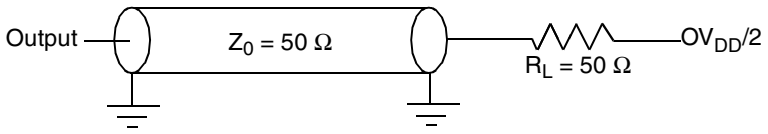


Figure 16. Local Bus C Test Load

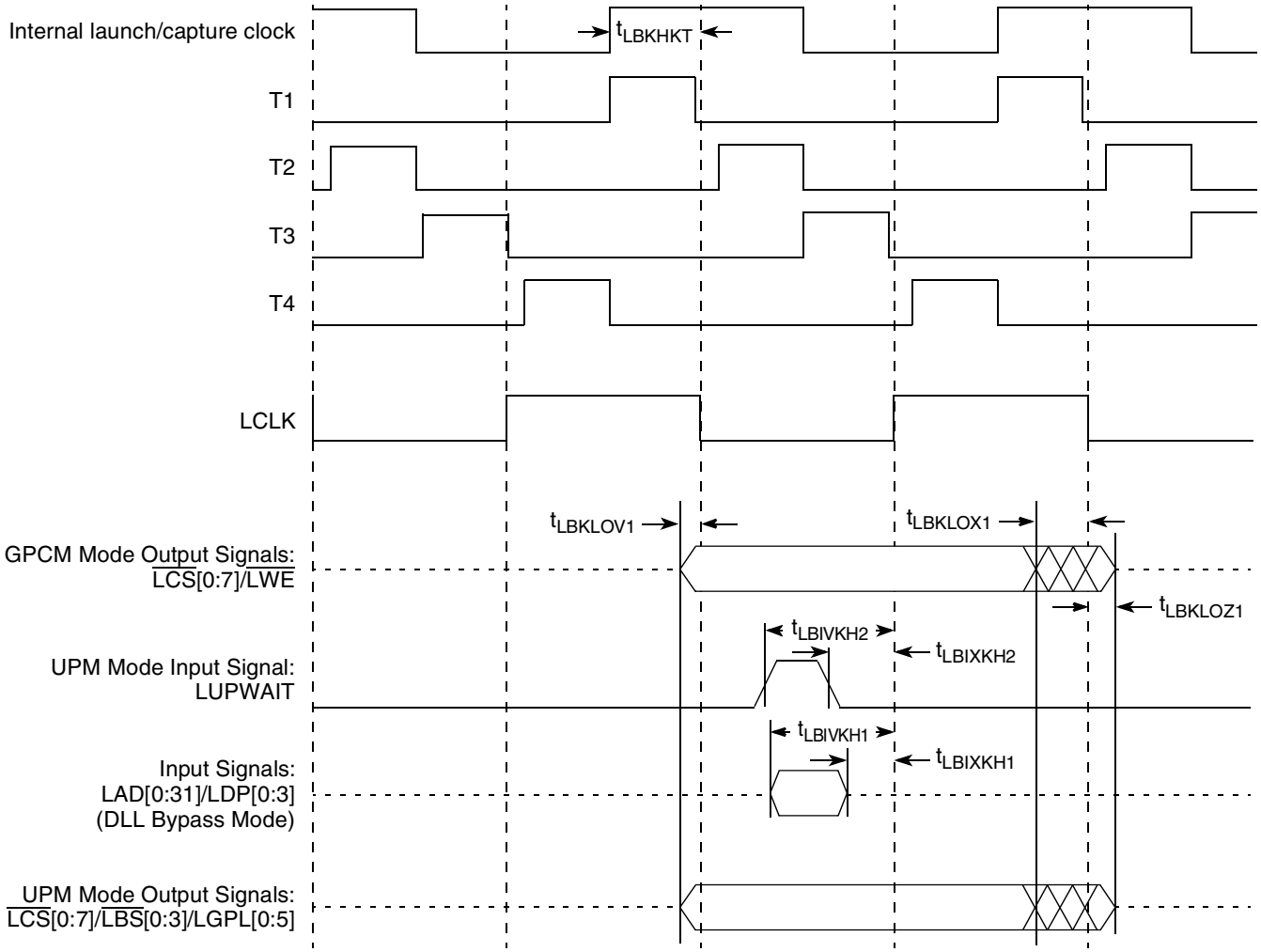


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 or 8 (DLL Bypass Mode)

Table 33. CPM Input AC Timing Specifications [1] (continued)

Characteristic	Symbol [2]	Min[3]	Unit
PIO inputs—input hold time	t_{PIIXKH}	1	ns
COL width high (FCC)	t_{FCCH}	1.5	CLK

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{FIIVKH} symbolizes the FCC inputs internal timing (FI) with respect to the time the input signals (I) reaching the valid state (V) relative to the reference clock t_{FCC} (K) going to the high (H) state or setup time.
3. PIO and TIMER inputs and outputs are asynchronous to SYSCLK or any other externally visible clock. PIO/TIMER inputs are internally synchronized to the CPM internal clock. PIO/TIMER outputs should be treated as asynchronous.

Table 34. CPM Output AC Timing Specifications [1]

Characteristic	Symbol [2]	Min	Max	Unit
FCC outputs—internal clock (NMSI) delay	t_{FIKHOX}	1	5.5	ns
FCC outputs—external clock (NMSI) delay	t_{FEKHOX}	2	8	ns
SPI outputs—internal clock (NMSI) delay	t_{NIKHOX}	0.5	10	ns
SPI outputs—external clock (NMSI) delay	t_{NEKHOX}	2	8	ns
PIO outputs delay	t_{PIKHOX}	1	11	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{FIKHOX} symbolizes the FCC inputs internal timing (FI) for the time t_{FCC} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 23 provides the AC test load for the CPM.

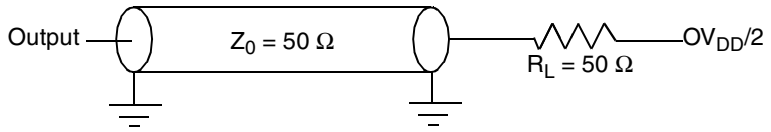


Figure 23. CPM AC Test Load

10.3 CPM I2C AC Specification

Table 35. I2C Timing

Characteristic	Expression	All Frequencies		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	0	F_{MAX}(1)	Hz
SCL clock frequency (master)	f_{SCL}	BRGCLK/16512	BRGCLK/48	Hz
Bus free time between transmissions	t_{SDHDL}	1/(2.2 * f_{SCL})	—	s
Low period of SCL	t_{SCLCH}	1/(2.2 * f_{SCL})	—	s
High period of SCL	t_{SCHCL}	1/(2.2 * f_{SCL})	—	s
Start condition setup time[2]	t_{SCHDL}	2/(divider * f_{SCL})	(2)	s
Start condition hold time[2]	t_{SDLCL}	3/(divider * f_{SCL})	—	s
Data hold time [2]	t_{SCLDX}	2/(divider * f_{SCL})	—	s
Data setup time[2]	t_{SDVCH}	3/(divider * f_{SCL})	—	s
SDA/SCL rise time	t_{SRISE}	—	1/(10 * f_{SCL})	s
SDA/SCL fall time	t_{SFALL}	—	1/(33 * f_{SCL})	s
Stop condition setup time	t_{SCHDH}	2/(divider * f_{SCL})	—	s

Notes:

1. F_{MAX} = BRGCLK/(min_divider*prescale. Where prescaler=25-I2MODE[PDIV]; and min_divider=12 if digital filter disabled and 18 if enabled.
   Example #1: if I2MODE[PDIV]=11 (prescaler=4) and I2MODE[FLT]=0 (digital filter disabled) then FMAX=BRGCLK/48
   Example #2: if I2MODE[PDIV]=00 (prescaler=32) and I2MODE[FLT]=1 (digital filter enabled) then FMAX=BRGCLK/576
2. divider = f_{SCL}/prescaler.
   In master mode: divider=BRGCLK/(f_{SCL}*prescaler)=2*(I2BRG[DIV]+3)
   In slave mode: divider=BRGCLK/(f_{SCL}*prescaler)

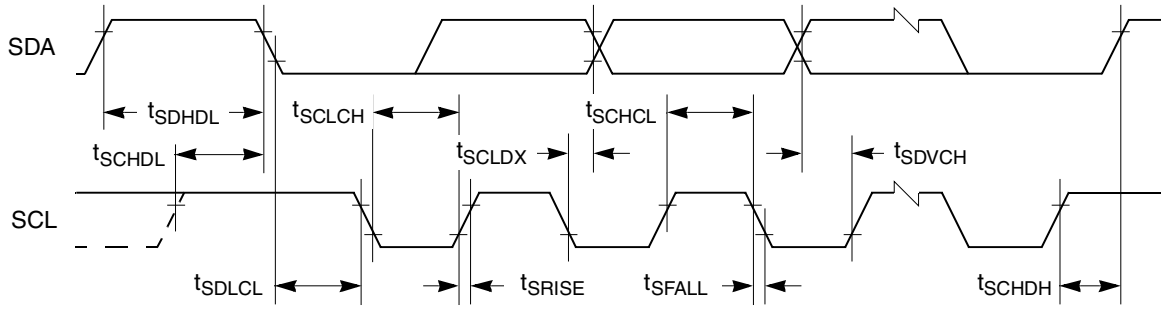


Figure 30. CPM I2C Bus Timing Diagram

Figure 31 provides the AC test load for TDO and the boundary-scan outputs of the MPC8541E.

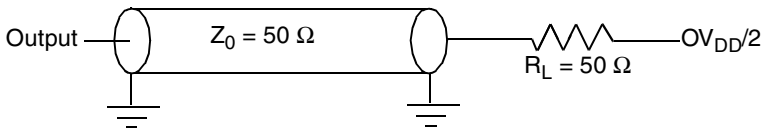


Figure 31. AC Test Load for the JTAG Interface

Figure 32 provides the JTAG clock input timing diagram.

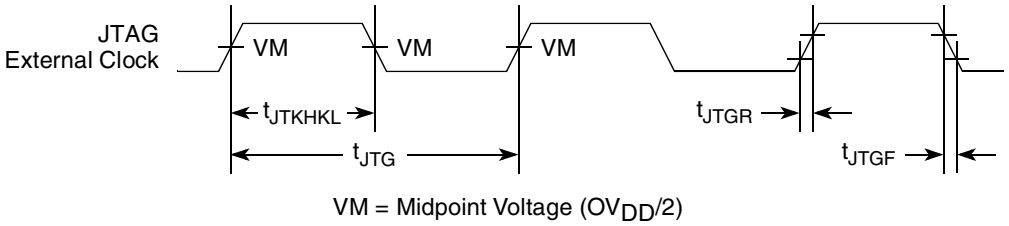


Figure 32. JTAG Clock Input Timing Diagram

Figure 33 provides the $\overline{\text{TRST}}$ timing diagram.

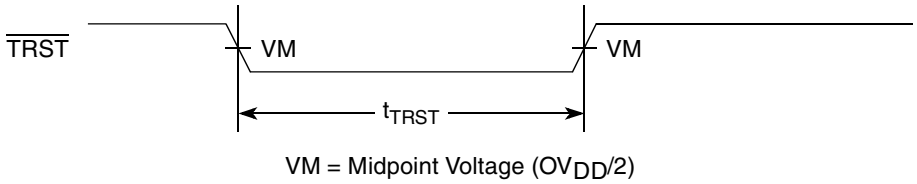


Figure 33. $\overline{\text{TRST}}$ Timing Diagram

Figure 34 provides the boundary-scan timing diagram.

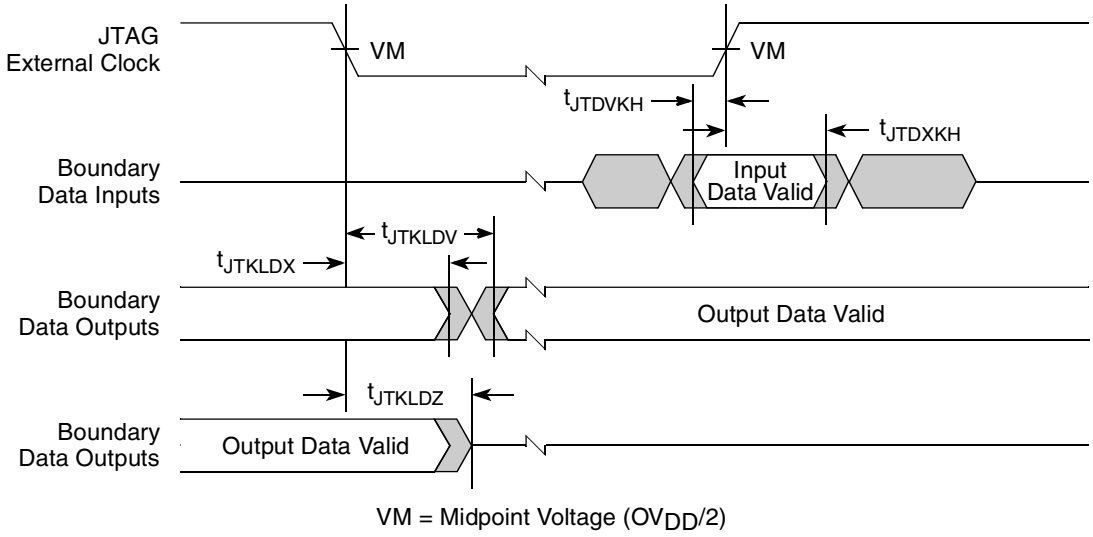


Figure 34. Boundary-Scan Timing Diagram

Figure 16 provides the AC test load for the I^2C.

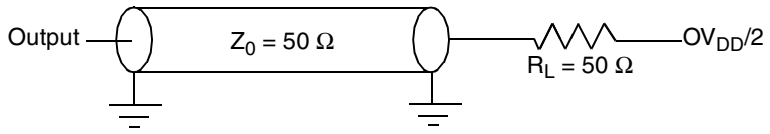


Figure 36. I^2C AC Test Load

Figure 37 shows the AC timing diagram for the I^2C bus.

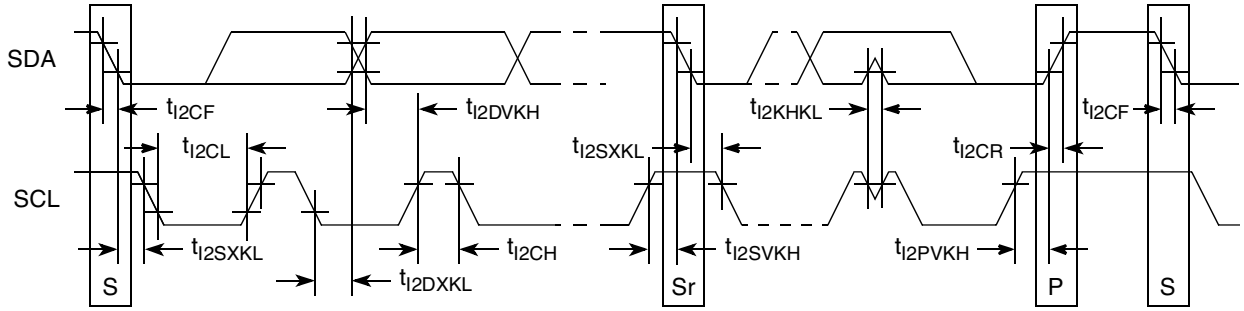


Figure 37. I^2C Bus AC Timing Diagram

13 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8541E.

13.1 PCI DC Electrical Characteristics

Table 41 provides the DC electrical characteristics for the PCI interface of the MPC8541E.

Table 41. PCI DC Electrical Characteristics [1]

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
Input current	I_{IN}	V_{IN} [2] = 0 V or $V_{IN} = V_{DD}$	—	±5	µA
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –100 µA	OV_{DD} – 0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 100 µA	—	0.2	V

Notes:
1. Ranges listed do not meet the full range of the DC specifications of the *PCI 2.2 Local Bus Specifications*.
2. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

15.3 e500 Core PLL Ratio

Table 47 describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LALE and LGPL2 at power up, as shown in Table 47.

Table 47. e500 Core to CCB Ratio

Binary Value of LALE, LGPL2 Signals	Ratio Description
00	2:1 e500 core:CCB
01	5:2 e500 core:CCB
10	3:1 e500 core:CCB
11	7:2 e500 core:CCB

15.4 Frequency Options

Table 48 shows the expected frequency values for the platform frequency when using a CCB to SYSCLK ratio in comparison to the memory bus speed.

Table 48. Frequency Options with Respect to Memory Bus Speeds

CCB to SYSCLK Ratio	SYSCLK (MHz)								
	17	25	33	42	67	83	100	111	133
	Platform/CCB Frequency (MHz)								
2							200	222	267
3					200	250	300	333	
4					267	333			
5				208	333				
6			200	250					
8		200	267	333					
9		225	300						
10		250	333						
12	200	300							
16	267								

Chanhassen, MN 55317
Internet: www.bergquistcompany.com

Thermagon Inc. 888-246-9050
4707 Detroit Ave.
Cleveland, OH 44102
Internet: www.thermagon.com

16.2.4 Heat Sink Selection Examples

The following section provides a heat sink selection example using one of the commercially available heat sinks.

16.2.4.1 Case 1

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_J = T_I + T_R + (\theta_{JC} + \theta_{INT} + \theta_{SA}) \times P_D$$

where

T_J is the die-junction temperature

T_I is the inlet cabinet ambient temperature

T_R is the air temperature rise within the computer cabinet

θ_{JC} is the junction-to-case thermal resistance

θ_{INT} is the adhesive or interface material thermal resistance

θ_{SA} is the heat sink base-to-ambient thermal resistance

P_D is the power dissipated by the device. See Table 4 and Table 5.

During operation the die-junction temperatures (T_J) should be maintained within the range specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_A) may range from 30° to 40°C. The air temperature rise within a cabinet (T_R) may be in the range of 5° to 10°C. The thermal resistance of some thermal interface material (θ_{INT}) may be about 1°C/W. For the purposes of this example, the θ_{JC} value given in Table 49 that includes the thermal grease interface and is documented in note 4 is used. If a thermal pad is used, θ_{INT} must be added.

Assuming a T_I of 30°C, a T_R of 5°C, a FC-PBGA package θ_{JC} = 0.96, and a power consumption (P_D) of 8.0 W, the following expression for T_J is obtained:

$$\text{Die-junction temperature: } T_J = 30°C + 5°C + (0.96°C/W + \theta_{SA}) \times 8.0\ W$$

The heat sink-to-ambient thermal resistance (θ_{SA}) versus airflow velocity for a Thermalloy heat sink #2328B is shown in Figure 46.

Assuming an air velocity of 2 m/s, we have an effective θ_{SA+} of about 3.3°C/W, thus

$$T_J = 30°C + 5°C + (0.96°C/W + 3.3°C/W) \times 8.0\ W,$$

resulting in a die-junction temperature of approximately 69°C which is well within the maximum operating temperature of the component.

When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

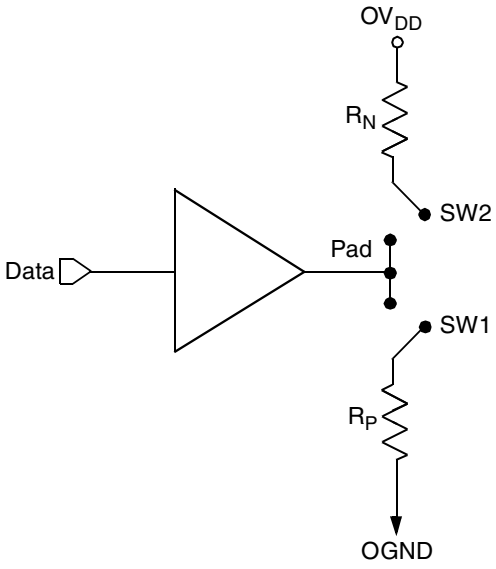


Figure 50. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = 1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

Table 50 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 50. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	43 Target	25 Target	20 Target	Z_0	Ω
R_P	43 Target	25 Target	20 Target	Z_0	Ω
Differential	NA	NA	NA	Z_{DIFF}	Ω

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

17.6 Configuration Pin Multiplexing

The MPC8541E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform/system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

17.7 Pull-Up Resistor Requirements

The MPC8541E requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins.

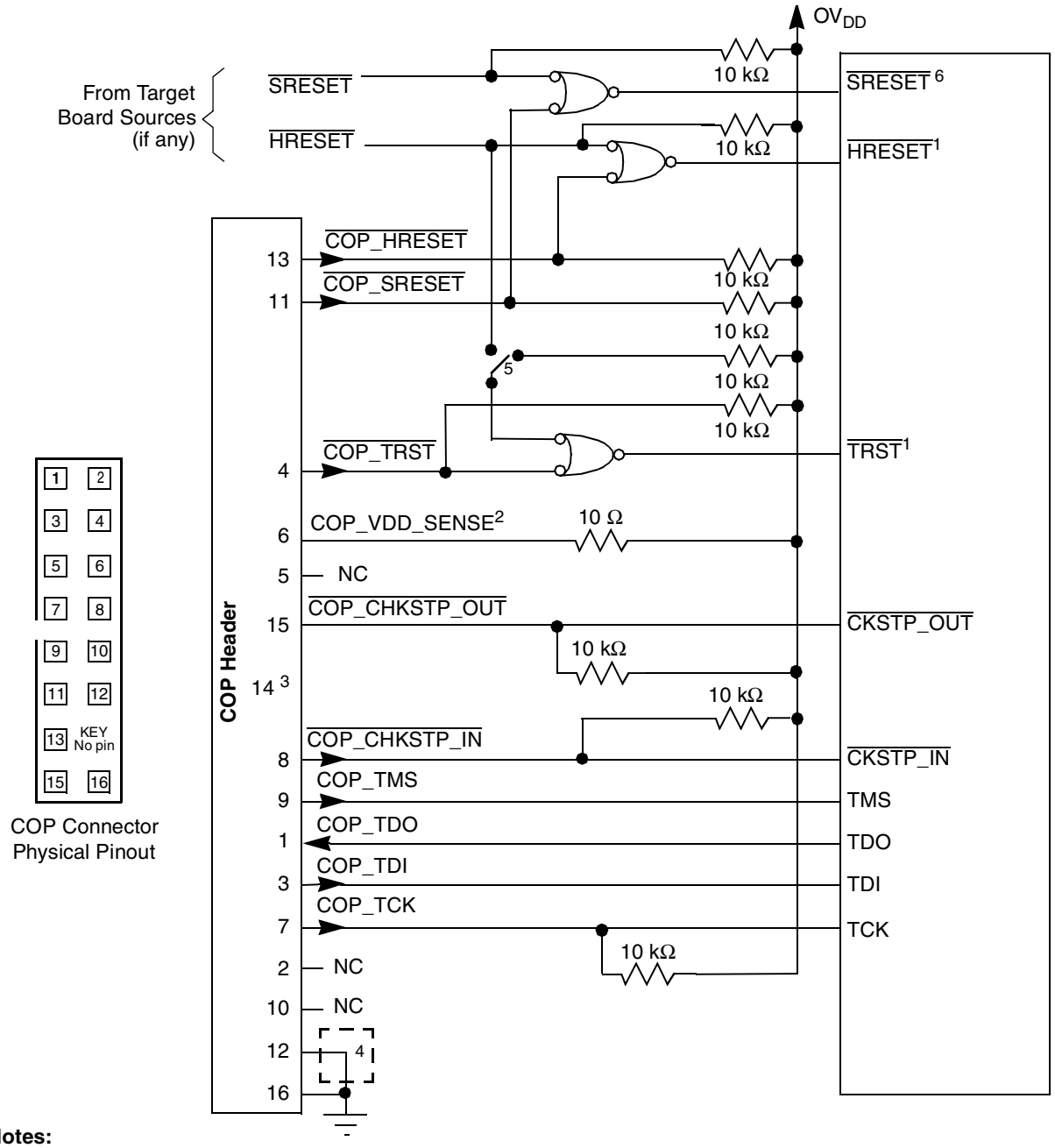
Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 52. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion give unpredictable results.

TSEC1_TXD[3:0] must not be pulled low during reset. Some PHY chips have internal pulldowns that could cause this to happen. If such PHY chips are used, then a pullup must be placed on these signals strong enough to restore these signals to a logical 1 during reset.

Refer to the PCI 2.2 specification for all pull-ups required for PCI.

17.8 JTAG Configuration Signals

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{\text{TRST}}$ signal is optional in the IEEE 1149.1 specification, but is provided on all processors that implement the Power Architecture. The device requires $\overline{\text{TRST}}$ to be asserted during reset conditions to ensure the JTAG boundary logic does not interfere with normal chip operation. While it is possible to force the TAP controller to the reset state using only the TCK and TMS signals, generally systems assert $\overline{\text{TRST}}$ during the power-on reset flow. Simply tying $\overline{\text{TRST}}$ to $\overline{\text{HRESET}}$ is not practical because the JTAG interface is also used for accessing the common on-chip processor (COP) function.



Notes:

1. The COP port and target board should be able to independently assert $\overline{\text{HRESET}}$ and $\overline{\text{TRST}}$ to the processor in order to fully control the processor as shown here.
2. Populate this with a 10 Ω resistor for short-circuit/current-limiting protection.
3. The KEY location (pin 14) is not physically present on the COP header.
4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
5. This switch is included as a precaution for BSDL testing. The switch should be open during BSDL testing to avoid accidentally asserting the $\overline{\text{TRST}}$ line. If BSDL testing is not being performed, this switch should be closed or removed.
6. Asserting $\overline{\text{SRESET}}$ causes a machine check interrupt to the e500 core.

Figure 52. JTAG Interface Connection

19 Device Nomenclature

Ordering information for the parts fully covered by this specification document is provided in Section 19.1, “Nomenclature of Parts Fully Addressed by this Document.”

19.1 Nomenclature of Parts Fully Addressed by this Document

Table 52 provides the Freescale part numbering nomenclature for the MPC8541E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number.

Table 52. Part Numbering Nomenclature

MPC	*nnnn*		*t*	*pp*	*aa*	*a*	*r*
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range[1]**	**Package [2]**	**Processor Frequency [3]**	**Platform Frequency**	**Revision Level[4]**
MPC	8541	Blank = not included E = included	Blank = 0 to 105°C C = –40 to 105°C	PX = FC-PBGA VT = FC-PBGA (lead free)	AJ = 533 MHz AK = 600 MHz AL = 667 MHz AP = 833 MHz AQ = 1000 MHZ	D = 266 MHz E = 300 MHz F = 333 MHz	

Notes:

1. For Temperature Range=C, Processor Frequency is limited to 667 MHz with a Platform Frequency selector of 333 MHz, Processor Frequency is limited to 533 MHz with a Platform Frequency selector of 266 MHz.
2. See Section 14, “Package and Pin Listings,” for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by Part Number Specifications may support other maximum core frequencies.
4. Contact you local Freescale field applications engineer (FAE).

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